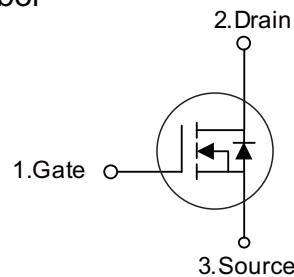


■ PRODUCT CHARACTERISTICS

VDSS	650V
R _{DS(on)} max(@V _{GS} = 10 V)	0.6Ω
Qg@type	13nC
ID	7A

Symbol

■ APPLICATIONS

- * Power factor correction
- * Switched mode power supplies
- * Uninterruptible power supply

■ FEATURES

- * low R_{DS(on)}
- * low gate charge
- * RoHS compliant



TO-252



TO-251

■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT65R600C	TO-251	70 pieces/Tube
N/A	MOT65R600D	TO-252	2500 pieces/Reel

■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V _{GS} = 0V)	V _{DSS}	650	V
Continuous Drain Current T _C = 25°C	I _D	7	A
TC = 100°C		4.2	
Pulsed Drain Current (note1)	I _{DM}	21	A
Gate-Source Voltage	V _{GSS}	±30	V
Single Pulse Avalanche Energy (note2)	E _{AS}	142	mJ
Repetitive Avalanche Energy (note2)	E _{AR}	0.21	mJ
Avalanche Current	I _{AR}	1.3	A
MOSFET dv/dt ruggedness, V _{DS} = 0...480V	dv/dt	50	V/ns
Power Dissipation	P _D	63	W
Continuous Body Diode Current	I _S	6	A
Pulsed Diode Forward Current (note1)	I _{SM}	21	
Reverse diode dv/dt (note3)	dv/dt	15	V/ns
Maximum diode commutation speed (note3)	di/dt	500	A/us
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150	°C

■ THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case max	R _{thjc}	2	°C/W
Thermal resistance, junction-ambient max	R _{thja}	62	°C/W



MOT65R600C-MOT65R600D N-CHANNEL MOSFET

■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	650	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 650\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 25^\circ\text{C}$	--	--	1	μA
		$V_{\text{DS}} = 650\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 150^\circ\text{C}$	--	--	100	
Gate-Source Leakage	I_{GSS}	$V_{\text{GS}} = \pm 30\text{V}$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	2.5	--	4.0	V
Drain-Source On-Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 3.5\text{A}$	--	0.53	0.6	Ω
Gate resistance	R_G	f = 1.0MHz open drain	--	19	--	Ω
Dynamic						
Input Capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 100\text{V}, f = 1.0\text{MHz}$	--	509	--	pF
Output Capacitance	C_{oss}		--	23	--	
Reverse Transfer Capacitance	C_{rss}		--	1.5	--	
Total Gate Charge	Q_g	$V_{\text{DD}} = 520\text{V}, I_D = 7\text{A}, V_{\text{GS}} = 10\text{V}$	--	13	--	nC
Gate-Source Charge	Q_{gs}		--	2.8	--	
Gate-Drain Charge	Q_{gd}		--	5.6	--	
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 400\text{V}, I_D = 7\text{A}, R_G = 25\Omega$	--	55	--	ns
Turn-on Rise Time	t_r		--	61	--	
Turn-off Delay Time	$t_{\text{d}(\text{off})}$		--	117	--	
Turn-off Fall Time	t_f		--	42	--	
Drain-Source Body Diode Characteristics						
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{\text{SD}} = 3.5\text{A}, V_{\text{GS}} = 0\text{V}$	--	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R = 400\text{V}, I_F = 7\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	--	321	--	ns
Reverse Recovery Charge	Q_{rr}		--	3.4	--	μC
Peak Reverse Recovery Current	I_{rrm}		--	21.2	--	A

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_{\text{AS}} = 2.4\text{A}, V_{\text{DD}} = 50\text{V}, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Identical low side and high side switch with identical R_G

■ TEST CIRCUITS AND WAVEFORMS

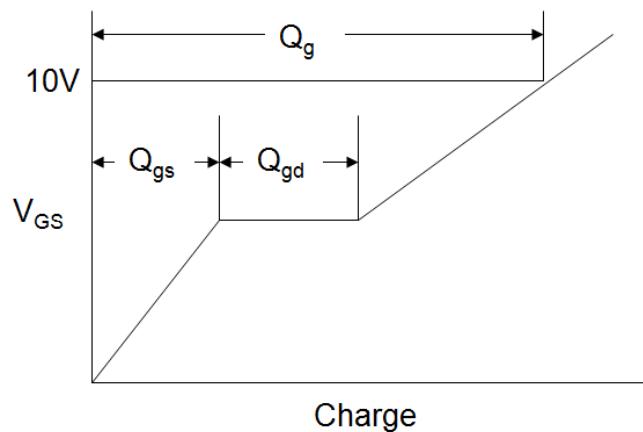
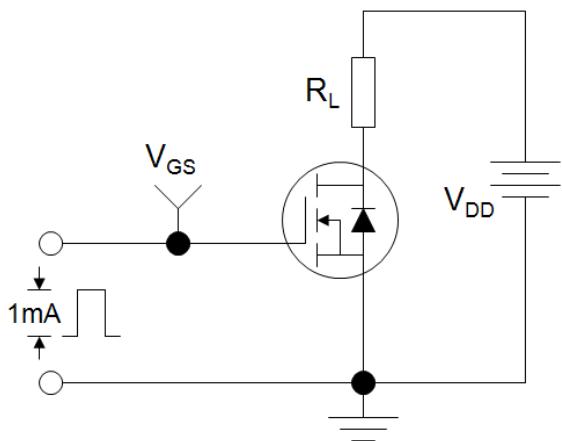


Figure A: Gate Charge Test Circuit and Waveform

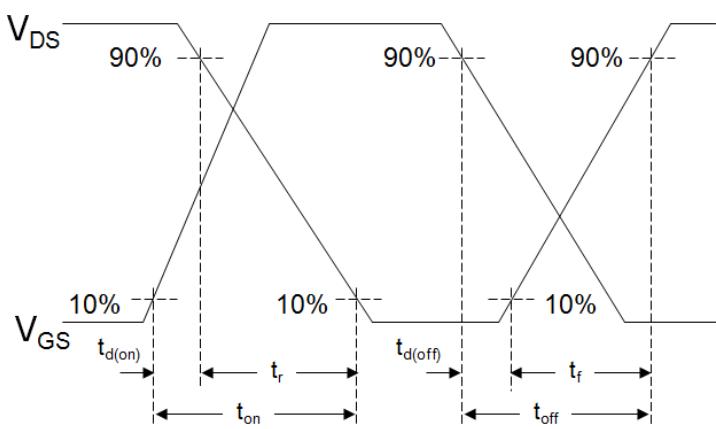
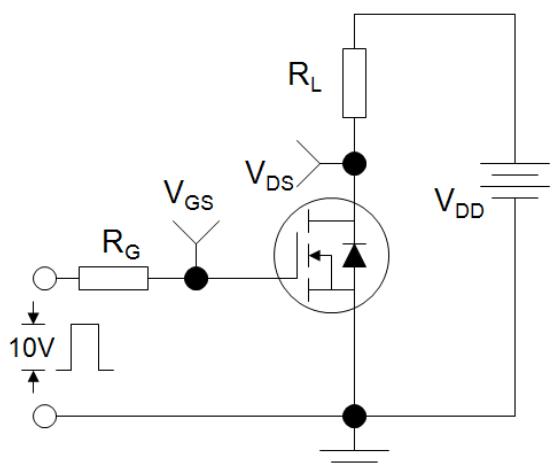


Figure B: Resistive Switching Test Circuit and Waveform

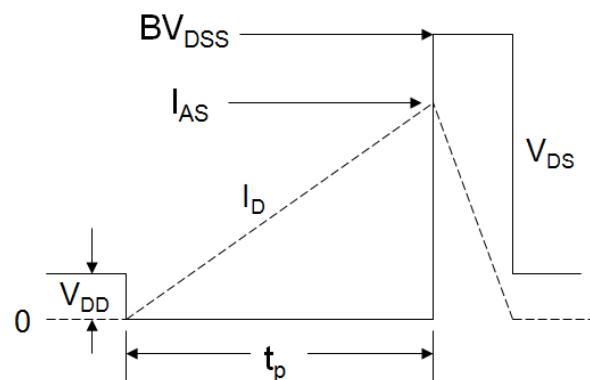
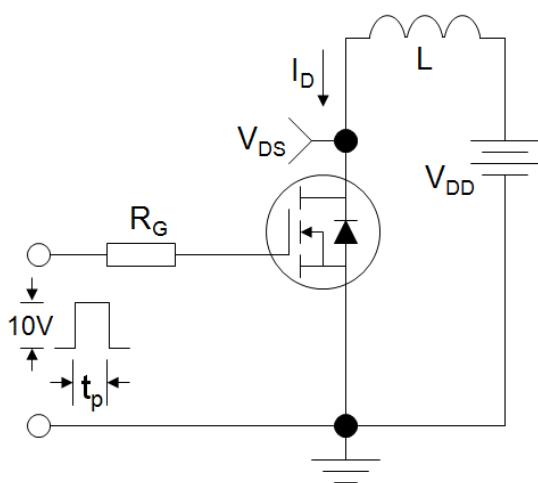
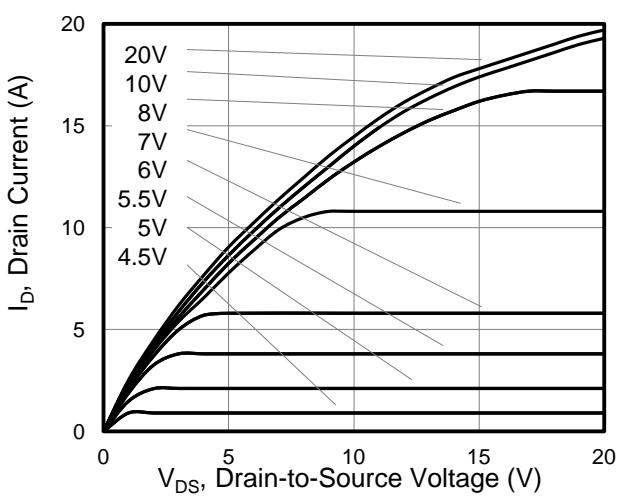
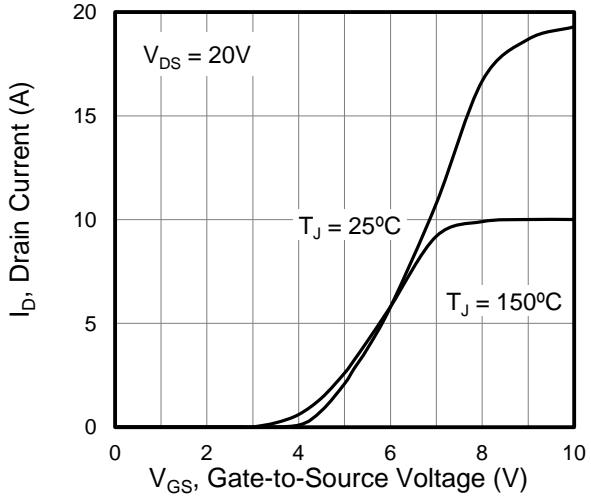
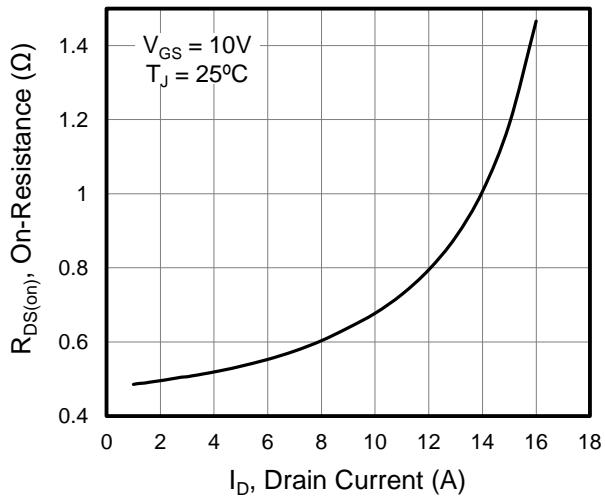
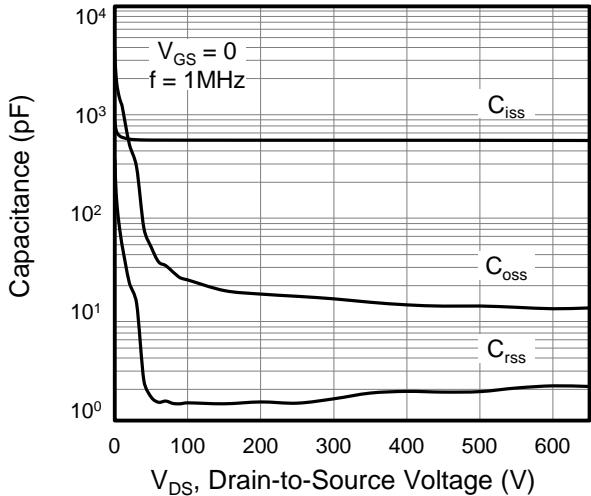
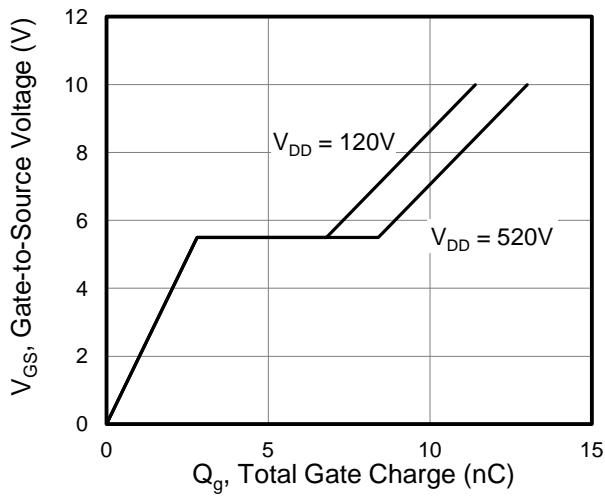
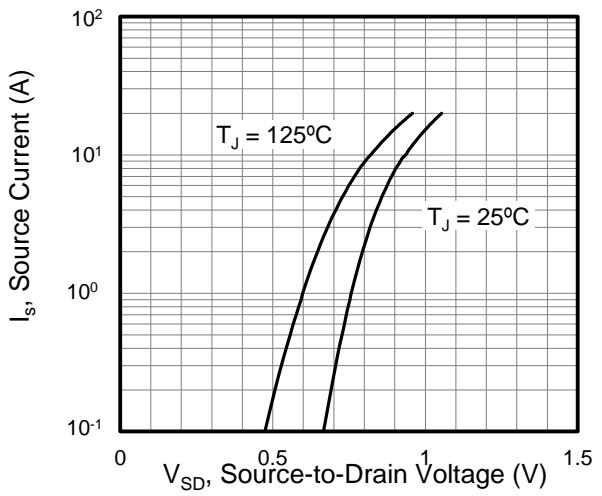
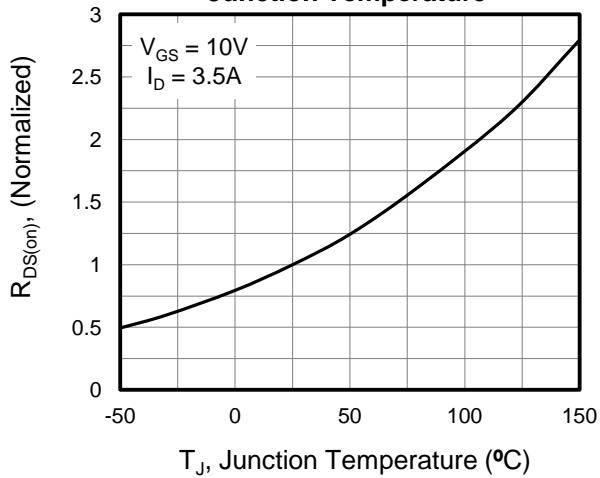
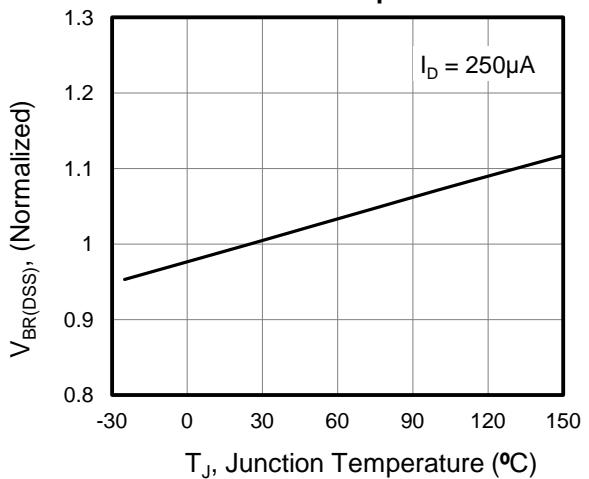
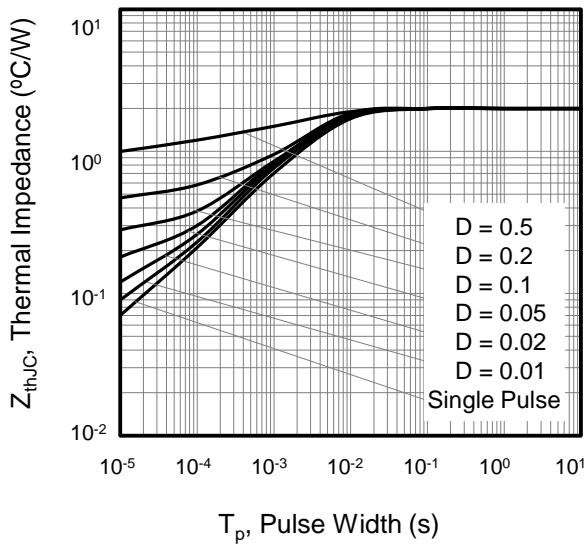
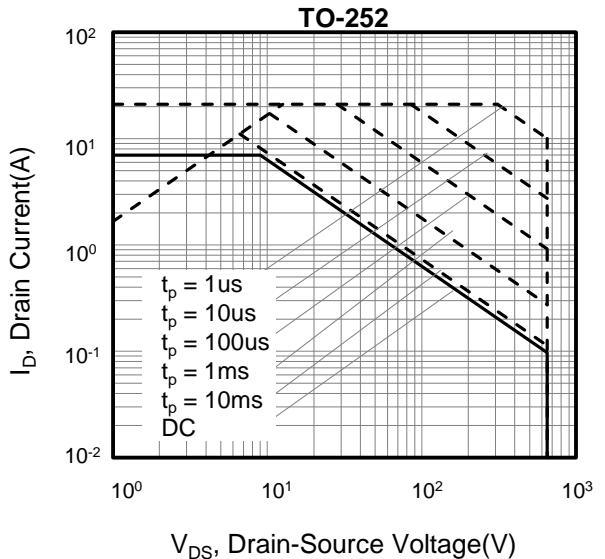


Figure C: Unclamped Inductive Switching Test Circuit and Waveform

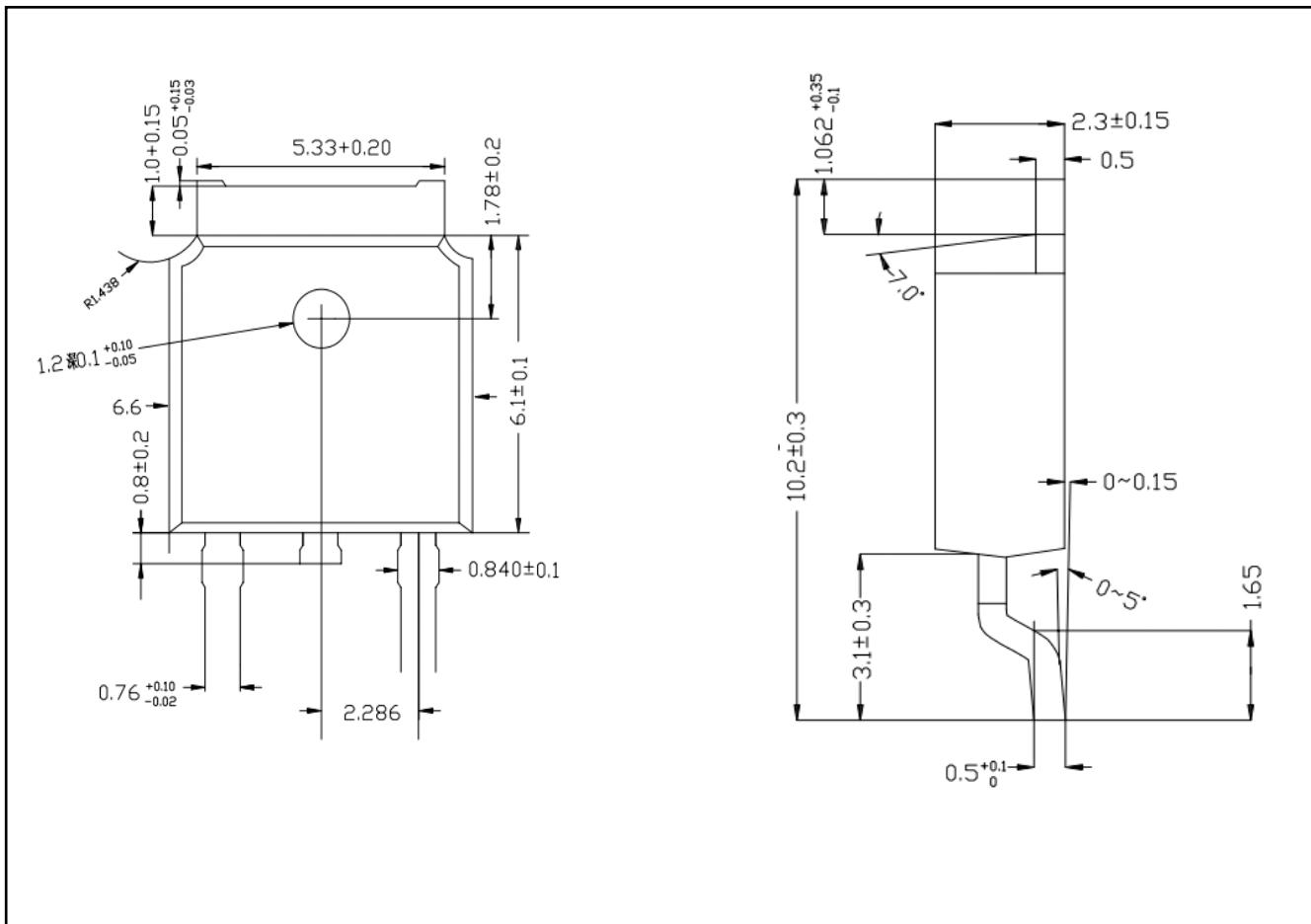
■ TYPICAL CHARACTERISTICS

Figure 1. Output Characteristics

Figure 2. Transfer Characteristics

Figure 3. On-Resistance vs. Drain Current

Figure 4. Capacitance

Figure 5. Gate Charge

Figure 6. Body Diode Forward Voltage


■ TYPICAL CHARACTERISTICS(Cont.)

**Figure 7. On-Resistance vs.
Junction Temperature**

**Figure 8. Breakdown voltage vs.
Junction Temperature**

**Figure 9. Transient Thermal Impedance
TO-252**

**Figure 10. Safe operation area for
TO-252**


■ TO-252-2L PACKAGE OUTLINE DIMENSIONS





MOT65R600C-MOT65R600D
N-CHANNEL MOSFET

■ TO-251-3L PACKAGE OUTLINE DIMENSIONS

